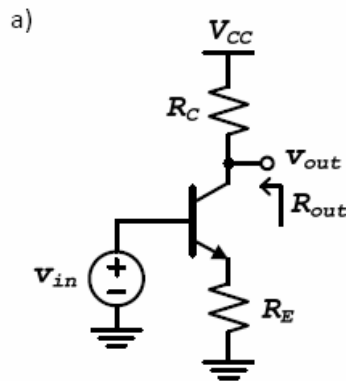


**Problem 1.1:** For each of the following circuits, find simplified expressions for gain ( $A_v = v_{out} / v_{in}$ ) and  $R_{out}$ . Solving by inspection is preferred. It is ok to keep parallel combinations of resistors in the form ( $R_1 || R_2$ ). For simplicity, assume that  $g_m$ ,  $r_o$ , and  $R_\pi$  are identical for all devices, ignore body effect, and ignore  $r_o$  when appropriate ( $1/g_m$ ,  $R_C$  and  $R_E \ll r_o$ ).



$G_m \equiv \text{effective } g_m$

$$G_m = \frac{\partial I_C}{\partial V_{in}} = \frac{\partial I_C}{\partial V_{BE}} \cdot \frac{\partial V_{BE}}{\partial V_{in}} = g_m \frac{\partial V_{BE}}{\partial V_{in}}, \quad V_{BE} = V_{in} - \alpha I_C R_E$$

$$G_m = g_m \frac{\partial}{\partial V_{in}} [V_{in} - \alpha I_C R_E] = g_m \left[ 1 - \alpha R_E \frac{\partial I_C}{\partial V_{in}} \right]$$

$$G_m = g_m [1 - \alpha R_E G_m] \Rightarrow G_m [1 + \alpha R_E g_m] = g_m$$

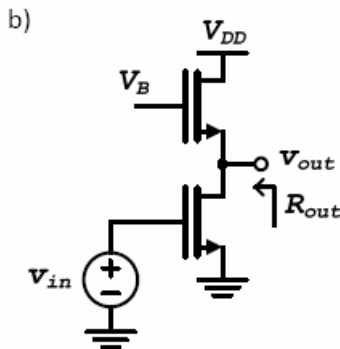
$$G_m = \frac{g_m}{1 + \alpha g_m R_E}, \quad \alpha \approx 1$$

$$G_m \approx \frac{g_m}{1 + g_m R_E}$$

$$R_{out} \approx R_C \quad \text{since } r_o \gg R_C$$

$$A_v = -G_m R_{out} = -\frac{g_m}{1 + g_m R_E} R_C$$

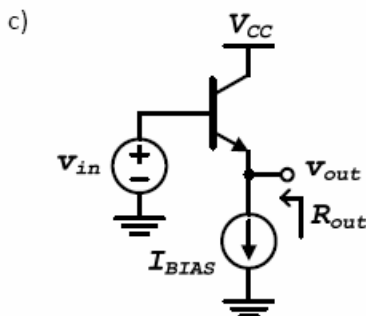
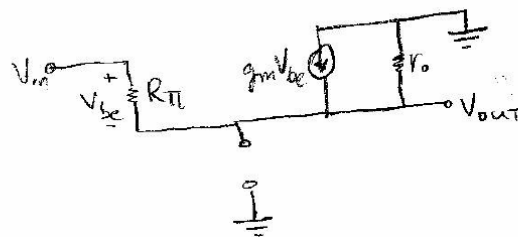
$$A_v = -\frac{g_m R_C}{1 + g_m R_E}$$



$$R_{out} = \frac{1}{g_m} || r_o \approx \frac{1}{g_m}$$

$$A_v = -g_m R_{out} \approx -g_m \left( \frac{1}{g_m} \right)$$

$$A_v \approx -1$$



$$V_{be} = V_{in} - V_{out}$$

$$V_{out} = g_m V_{be} r_o = g_m r_o (V_{in} - V_{out})$$

$$V_{out} (1 + g_m r_o) = V_{in} g_m r_o$$

$$A_v = \frac{V_{out}}{V_{in}} = \frac{g_m r_o}{1 + g_m r_o}, \quad g_m r_o \gg 1$$

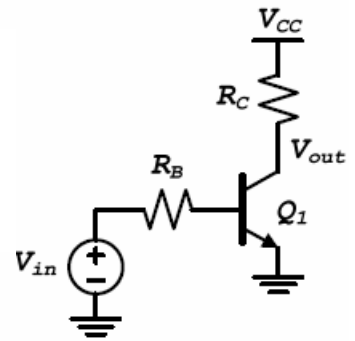
$$A_v \approx 1$$

$$R_{out} = R_C || \frac{1}{g_m} || r_o, \quad r_o \gg R_C \gg \frac{1}{g_m}$$

$$R_{out} \approx \frac{1}{g_m}$$

**Problem 1.2:** Use the circuit on the right for this problem. Include base width modulation in your calculations. Assume  $\beta_F = 120$ ,  $V_A = 35\text{V}$ ,  $V_{CE(sat)} = 0.3\text{V}$ , and  $V_{BE} = 0.7\text{V}$  when  $Q_1$  is in the forward active region.

- a) Find the DC values of  $I_B$ ,  $I_C$ , and  $V_{out}$  at the quiescent point. Assume  $V_{in} = 2.7\text{V}$ ,  $R_B = 100\text{k}\Omega$ ,  $V_{CC} = 5\text{V}$ , and  $R_C = 1\text{k}\Omega$ . What region is  $Q_1$  operating in?



$$I_B = \frac{V_{in} - V_{BE}}{R_B} \quad I_C = \beta I_B \left(1 + \frac{V_{CE}}{V_A}\right) \quad I_C = \frac{V_{CC} - V_{out}}{R_C}$$

$$I_B = \frac{2.7 - 0.7}{100\text{k}} = 20\mu\text{A}$$

$$V_A = 35\text{V}$$

$$V_{CC} = 5\text{V}$$

$$\beta = 120$$

$$R_C = 1\text{k}\Omega$$

$$R_B = 100\text{k}\Omega$$

$$\beta I_B \left(1 + \frac{V_{out}}{V_A}\right) = \frac{V_{CC} - V_{out}}{R_C}, \quad V_{out} = V_{CE}$$

$$V_{out} = V_A \left[ \frac{V_{CC} - \beta I_B R_C}{\beta I_B R_C + V_A} \right]$$

$$V_{out} \approx 2.433\text{V}$$

$$I_C = \frac{V_{CC} - V_{out}}{R_C} = 2.567\text{mA}$$

Since  $V_{CE} = V_{out} \approx 2.433 > V_{CE(sat)} \therefore$  forward active

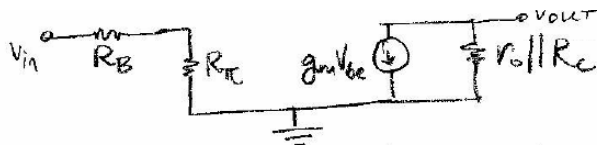
- b) Find the values of  $g_m$ ,  $R_{\pi}$ , and  $r_o$  at the quiescent point found in part a) and room temperature.

$$g_m = \frac{I_C}{V_T} \approx \frac{2.567\text{mA}}{26\text{mV}} \approx 98.7\text{mS}$$

$$R_{\pi} = \frac{\beta}{g_m} = \frac{120}{98.7\text{m}} \approx 1.216\text{k}\Omega$$

$$r_o = \frac{V_A}{I_C} = \frac{35}{2.567\text{mA}} \approx 13.365\text{k}\Omega$$

- c) Derive a small signal expression for  $v_{out}/v_{in}$ , you do not need to solve for the numerical value.

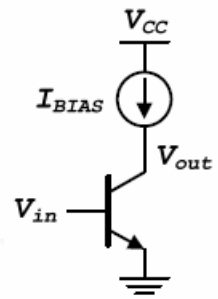


$$v_{out} = -g_m v_{be} (r_o \parallel R_C), \quad v_{be} = v_{in} \left( \frac{R_{\pi}}{R_{\pi} + R_B} \right)$$

$$v_{out} = -g_m v_{in} \left( \frac{R_{\pi}}{R_{\pi} + R_B} \right) (r_o \parallel R_C)$$

$$A_v = \frac{v_{out}}{v_{in}} = -g_m (r_o \parallel R_C) \left( \frac{R_{\pi}}{R_{\pi} + R_B} \right)$$

**Problem 1.3:** Use the circuit on the right for this problem. Assuming the transistor is biased in the forward active region, calculate the numerical value for small signal gain given  $V_A = 35V$ . Assume room temperature. This is the intrinsic gain of the device.

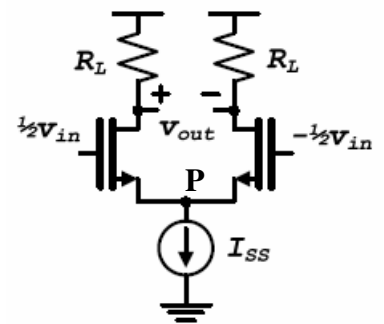


$$I_{Bias} = I_C = \beta I_B = \beta \frac{V_{IN}}{R_{\pi}} \quad I_C = g_m V_T \quad R_{\pi} = \frac{\beta}{g_m}$$

$$V_{OUT} = (I_C)(r_o) = \left(\beta \frac{V_{IN}}{R_{\pi}}\right) \left(\frac{V_A}{I_C}\right) = \left(\frac{\beta V_{IN}}{\beta/g_m}\right) \left(\frac{V_A}{g_m V_T}\right) = V_{IN} \left[ \frac{V_A}{V_T} \right]$$

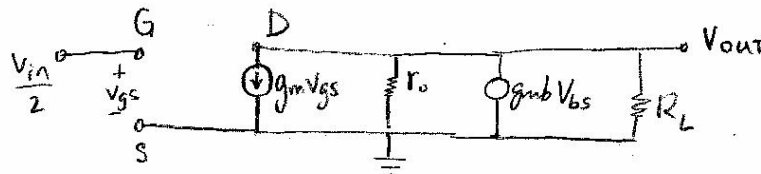
$$A_v = \frac{V_{OUT}}{V_{IN}} = \frac{V_A}{V_T} = \frac{35}{26m} \approx 1346.15 \text{ V/V}$$

**Problem 1.4:** Use the circuit on the right for this problem. Assume the circuit is symmetric.



- a) Draw the small signal half-circuit of the diff pair. Include channel length modulation and body effect in your model.

\* Point P looks like AC gnd.



- b) Find an expression for gain  $v_{out}/v_{in}$ .

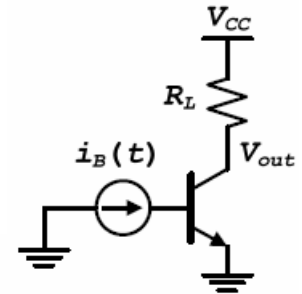
$$A_v = -g_m (R_L || r_o)$$

$$A_v \approx -g_m R_L$$

**Problem 1.5:** For this problem, use the parameter values given in the table below. Use the charge control model to solve the following parts.

Parameter	NPN	Units
$\beta_F$	100	A/A
$\beta_R$	10	A/A
$\tau_F$	10	ps
$\tau_R$	5	ns
$V_{CE(sat)}$	0	V

- a) For the circuit on the right, assume  $i_B$  is initially 0, and steps from 0 to  $10\mu A$  at time 0s and remains at  $10\mu A$ .  $V_{CC} = 5V$  and  $R_L = 2k\Omega$ . What region will the transistor be in at  $t = \infty$ ? Calculate the final values of  $q_F$  (in Coulombs),  $i_C$ , and  $V_{OUT}$ .



$$V_{CC} = 5V \quad R_L = 2k\Omega \quad I_B = 0 \rightarrow 10\mu A$$

$$i_C = \beta_F I_B (1 - e^{-t/\tau_{BF}})$$

$$\text{At } t = \infty \rightarrow i_C = \beta_F I_B (1 - e^{-\infty}) = \beta_F I_B$$

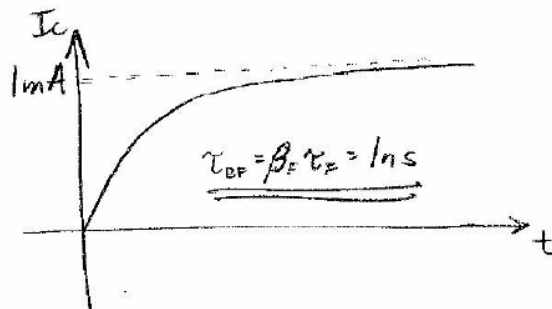
$$i_C = 100 (10\mu A) = \boxed{1mA}$$

$$q_F = i_C \tau_F = (1mA)(10p) = \boxed{1 \times 10^{-14} C}$$

$$V_{OUT} = V_{CC} - I_C R_L = 5 - (1mA)(2k) = \boxed{3V}$$

$$\therefore \boxed{\text{forward active}}$$

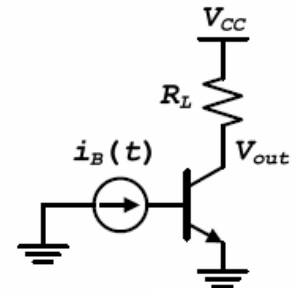
- b) Sketch the transient current  $i_C$  from part a) as a function of time. What is the time constant of the response?



**Problem 1.6:** For this problem, use the parameter values given in the table below. Use the charge control model to solve the following parts.

Parameter	NPN	Units
$\beta_F$	100	A/A
$\beta_R$	10	A/A
$\tau_F$	10	ps
$\tau_R$	5	ns
$V_{CE(sat)}$	0	V

- a) Now assume  $i_B$  is initially 0, and steps from 0 to  $100\mu A$  at time 0s and remains at  $100\mu A$ .  $V_{CC} = 5V$  and  $R_L = 2k\Omega$ . The BJT will obviously be in saturation at  $t = \infty$ . Using the charge control models in the saturation region, calculate the final values of  $q_{TOTAL} = q_F + q_R$ ,  $i_C$ , and  $v_{OUT}$ . Hint:  $I_C$  is determined by the circuit, and at time  $t = \infty$  (steady state), all  $dq/dt$  terms equal 0.



$$I_C = \frac{V_{CC} - V_{CE(sat)}}{R_L} = \frac{5}{2k} = 2.5mA$$

At  $t = \infty$

$$I_C = \frac{q_F}{\tau_F} - q_R \left[ \frac{1}{\beta_R \tau_R} + \frac{1}{\tau_R} \right] = \frac{q_F}{10p} - q_R \left[ \frac{1}{50n} + \frac{1}{5n} \right]$$

$$I_C = (1.1 \times 10^{12}) q_F - (2.2 \times 10^9) q_R = 2.5 \times 10^{-3} \quad (1)$$

$$I_B = \frac{q_F}{\beta_F \tau_F} + \frac{q_R}{\beta_R \tau_R} = \frac{q_F}{1n} + \frac{q_R}{50n}$$

$$I_B = (10^9) q_F + (2 \times 10^9) q_R = 100 \times 10^{-6} \quad (2)$$

Solving equations (1) and (2) simultaneously gives

$$q_R = 3.378pC \quad \text{and} \quad q_F = 0.032pC$$

$$\text{Then } q_{total} = q_F + q_R = \boxed{3.41pC}$$

$$I_C = i_C(t = \infty) = \boxed{2.5mA}$$

$$V_{OUT} = V_{CE(sat)} = \boxed{0V}$$

- b) At time  $t = 0$  the base charge is 0 and the device is in the forward active region. Let's assume for now that the device will remain in forward active and not saturate. Calculate the final value of  $i_c$  and  $V_{out}$  using the *forward active charge control models* ( $V_{out}$  will be negative). Sketch  $V_{out}$  as a function of time, and indicate what the time constant of the response is. Calculate the time at which  $V_{out}$  reaches the saturation voltage 0V.

→ At  $t = \infty$

$$I_B = 100 \mu A = \frac{q_F}{\tau_F \beta_F} = \frac{q_F}{1n} \rightarrow q_F = 0.1 pC$$

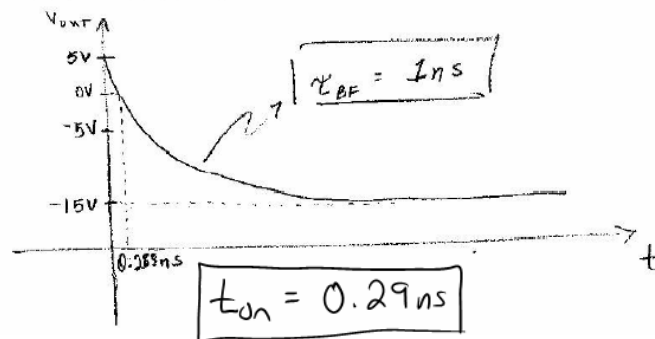
$$I_C = \frac{q_F}{\tau_F} = \frac{0.1 p}{10 p} = 0.01 \rightarrow \boxed{I_C = 10 mA}$$

$$V_{out} = V_{CC} - I_C R_L = 5 - (10 mA)(2k) = \boxed{-15V}$$

→ To sketch  $V_{out}$

$$V_{out} = V_{CC} - i_C R_L = V_{CC} - R_L \beta_F I_B (1 - e^{-t/\beta_F \tau_F})$$

$$V_{out} = 5 - (20)(1 - e^{-10^9 t})$$



- c) The base charge just prior to the onset of saturation is defined as  $q_{B0}$ . In part b), you calculated the time at which the BJT transitions from forward active to saturation. Calculate  $q_{B0}$  using the forward active region charge control model. Calculate  $i_{B0}$ , which is the value of base current that biases the BJT right at the edge of saturation.

Hint:  $i_C$  is determined by the circuit, and  $q_{B0} = q_F$  when  $V_{CE} = V_{CE(sat)}$ .

After  $t \approx 0.288 ns$ , BJT is at edge of saturation

$$i_C(t = 0.288 ns) = 100(100 \mu A)(1 - e^{-(10^9)(0.288 ns)}) = 2.5 mA$$

$$q_{B0} = q_F(t = 0.288 ns) = \tau_F i_C(0.288 ns) = (10 p)(2.5 mA)$$

$$\boxed{q_{B0} = 0.025 pC}$$

$$i_{B0} = \frac{i_C(t = 0.288 ns)}{\beta_F} = \frac{2.5 mA}{100}$$

$$\boxed{i_{B0} = 25 \mu A}$$

- d) You now have enough information to calculate the value of  $q_s$ , the excess charge stored in the base at time  $t = \infty$ , assuming now that the BJT goes into saturation.

$$q_{total} = q_{B0} + q_s$$

$$q_s = q_{total} - q_{B0} = 3.41 p - 0.025 p$$

$$\boxed{q_s = 3.385 pC}$$

- e) Now assume the base current is switched back to 0 after  $q_s$  has been stored in the base. With  $i_B = 0$ , the differential equation for  $q_s$  becomes:  $-i_{B0} = q_s/\tau_s + q_s/dt$ . The final value of  $q_s$  from this equation is  $-i_{B0}\tau_s$ . In reality, a negative  $q_s$  is not allowed, and instead the device will enter the forward active region when  $q_s = 0$ . However, we use this final value to find the time when  $q_s = 0$ . Sketch the solution to the above differential equation with an initial value of  $q_s$  found in d), and the final value of  $-i_{B0}\tau_s$ . Calculate the value of  $\tau_s$ . Now calculate the time at which  $q_s = 0$ . This is the time required to bring the BJT out of saturation, after which it will enter the forward active region and  $v_{out}$  begins to rise.

$$-i_{B0} = q_s/\tau_s + q_s/dt$$

$$(1) \frac{dq_{sp}}{dt} + \frac{1}{\tau_s} q_{sp} = -i_{B0}, \quad (2) \frac{dq_{sc}}{dt} + \frac{1}{\tau_s} q_{sc} = 0, \quad \begin{matrix} q_{sp} = \text{particular solution} \\ q_{sc} = \text{complementary solution} \end{matrix}$$

→  $q_{sp}$  must be a constant since  $-i_{B0}$  is constant. Therefore,

$$q_{sp} = -i_{B0}\tau_s$$

→ Rearranging equation (2), we get

$$\frac{dq_{sc}/dt}{q_{sc}} = \frac{-1}{\tau_s}$$

$$\frac{d}{dt}[\ln q_{sc}] = \frac{-1}{\tau_s}$$

$$\ln q_{sc} = \frac{-t}{\tau_s} + C$$

$$q_{sc} = e^C e^{-t/\tau_s} = K e^{-t/\tau_s}$$

→ To calculate  $K$ , the initial condition is  $q_s(t=0) = q_{s0}$  (from part d)

$$q_s(t) = q_{sp} + q_{sc} = -i_{B0}\tau_s + K e^{-t/\tau_s} = q_{s0}$$

$$K = q_{s0} + i_{B0}\tau_s$$

$$q_s(t) = -i_{B0}\tau_s + (q_{s0} + i_{B0}\tau_s) e^{-t/\tau_s}$$

$$q_s(t) = -i_{B0}\tau_s (1 - e^{-t/\tau_s}) + q_{s0} e^{-t/\tau_s}$$

$$i_{B0} = 25 \mu A$$

$$q_{s0} = 3.385 \text{ pC}$$

$$\tau_s = \beta_F \tau_{DE} + (1 + \beta_F) \tau_{BF}$$

$$\tau_s = \frac{1 + \beta_F + \beta_R}{\dots} = 45.14 \text{ ns}$$

$$\text{For } q_s(t) = 0 \rightarrow t \approx 62.57 \text{ ns}$$

